

Jue Wang

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Sidewall-Implanted Trench Termination for 4H-SiC Devices With High Breakdown Voltage and Low Leakage Current. IEEE Electron Device Letters, 2022, 43, 104-107.	3.9	6
2	Investigation of SiC Trench MOSFETs's Reliability under Short-Circuit Conditions. Materials, 2022, 15, 598.	2.9	0
3	Degradation of 4H-SiC Trench MOSFET under single and repetitive short-circuit stress. , 2021, , .		0
4	A Novel SiC LDMOS with Electric Field Optimization by Step Doping Technology. , 2020, , .		2
5	Design and Characterization of Area-Efficient Trench Termination for 4H-SiC Devices. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2019, 7, 1519-1526.	5.4	6
6	Investigation of 1200 V SiC MOSFETs's Surge Reliability. Micromachines, 2019, 10, 485.	2.9	22
7	Correction to "Trench Termination With SiO ₂ -Encapsulated Dielectric for Near-Ideal Breakdown Voltage in 4H-SiC Devices" [Dec 18 1900-1903]. IEEE Electron Device Letters, 2019, 40, 353-353.	3.9	0
8	Experimental Demonstration and Analysis of a 1.35-kV 0.92-m $\Omega \cdot \text{cm}^2$ SiC Superjunction Schottky Diode. IEEE Transactions on Electron Devices, 2018, 65, 1458-1465.	3.0	25
9	Trench Termination With SiO ₂ -Encapsulated Dielectric for Near-Ideal Breakdown Voltage in 4H-SiC Devices. IEEE Electron Device Letters, 2018, 39, 1900-1903.	3.9	16